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BUK754R0-40C

N-channel TrenchMOS standard level FET

Rev. 02 — 20 July 2010 **Product data sheet**

1. Product profile

1.1 General description

Standard level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Avalanche robust
- Suitable for standard level gate drive
- Suitable for thermally demanding environment up to 175°C rating

1.3 Applications

- 12V Motor, lamp and solenoid loads
- High performance automotive power systems
- High performance Pulse Width Modulation (PWM) applications

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	-	40	V
I_D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; see Figure 1; see Figure 3	[1]	-	-	100	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; see Figure 2		-	-	203	W
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 11; see Figure 12		-	3.4	4	mΩ

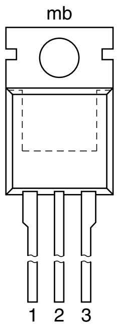
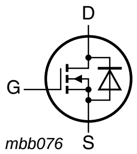
Table 1. Quick reference data *...continued*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 100 A; V_{sup} ≤ 40 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	-	292	mJ
Dynamic characteristics						
Q_{GD}	gate-drain charge	V_{GS} = 10 V; I_D = 25 A; V_{DS} = 32 V; T_j = 25 °C; see Figure 14; see Figure 13	-	35	-	nC

[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

SOT78 (TO-220AB)

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK754R0-40C	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	40	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20$ kΩ		-	40	V
V_{GS}	gate-source voltage		[1]	-20	20	V
I_D	drain current	$T_{mb} = 25$ °C; $V_{GS} = 10$ V; see Figure 1; see Figure 3	[2]	-	159	A
		$T_{mb} = 100$ °C; $V_{GS} = 10$ V; see Figure 1	[3]	-	100	A
		$T_{mb} = 25$ °C; $V_{GS} = 10$ V; see Figure 1; see Figure 3	[3]	-	100	A
I_{DM}	peak drain current	$T_{mb} = 25$ °C; $t_p \leq 10$ µs; pulsed; see Figure 3		-	636	A
P_{tot}	total power dissipation	$T_{mb} = 25$ °C; see Figure 2		-	203	W
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
Source-drain diode						
I_S	source current	$T_{mb} = 25$ °C	[3]	-	100	A
			[2]	-	159	A
I_{SM}	peak source current	$t_p \leq 10$ µs; pulsed; $T_{mb} = 25$ °C		-	636	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 100$ A; $V_{sup} \leq 40$ V; $R_{GS} = 50$ Ω; $V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; unclamped		-	292	mJ

[1] -20V accumulated duration not to exceed 168 hrs

[2] Current is limited by power dissipation chip rating.

[3] Continuous current is limited by package.

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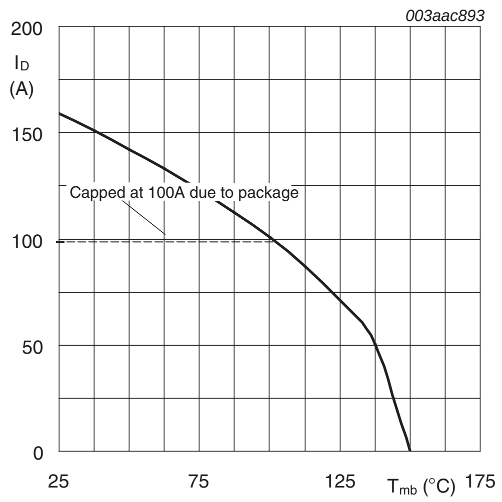
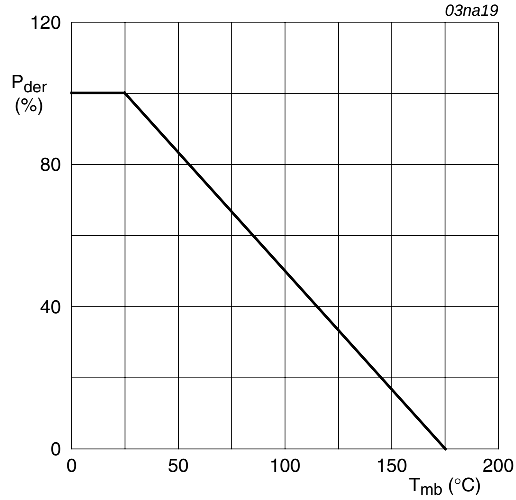


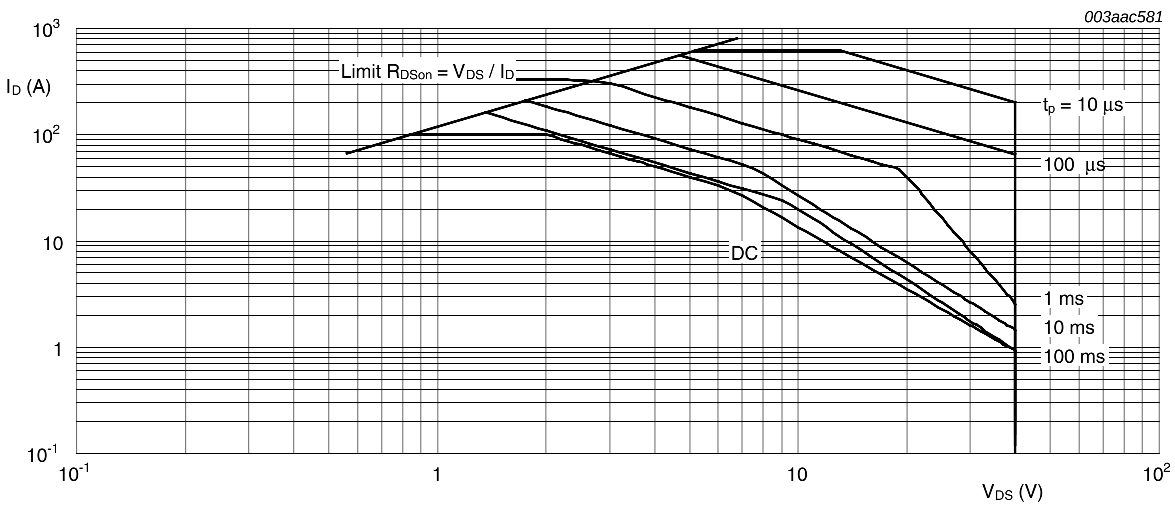
$$I_{der} = \frac{I_D}{I_{D(25°C)}} \times 100\,\%$$

Fig 1. Normalized continuous drain current as a function of mounting base temperature.



$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$$T_{mb} = 25°C; I_{DM} \text{ is single pulse}$$

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.74	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in still air	-	-	60	K/W

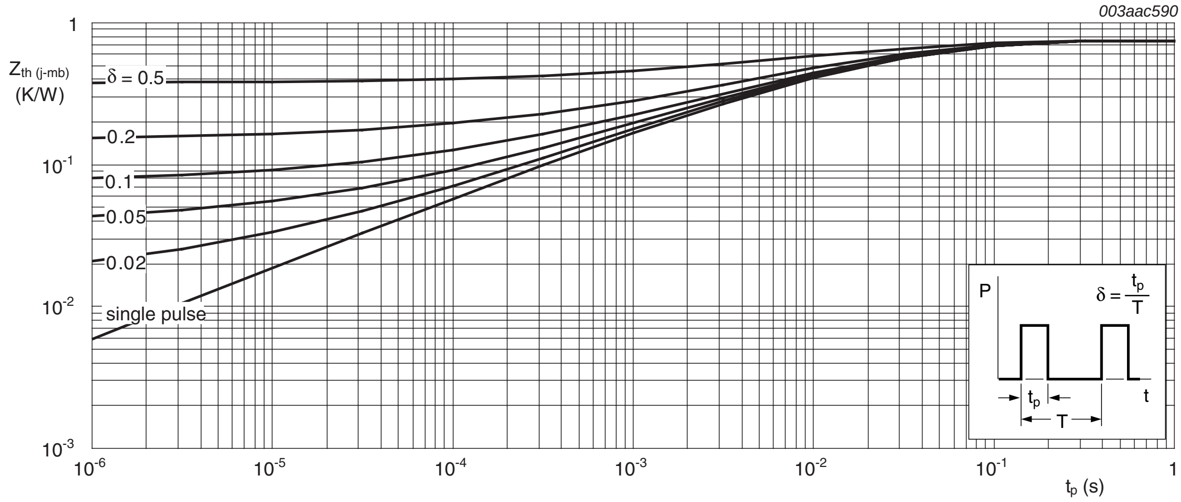

Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

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6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 0.25 mA; V_{GS} = 0 V; T_j = 25 °C	40	-	-	V
		I_D = 0.25 mA; V_{GS} = 0 V; T_j = -55 °C	36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; see Figure 10	2	3	4	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; see Figure 10	1	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; see Figure 10	-	-	4.4	V
I_{DSS}	drain leakage current	V_{DS} = 40 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	µA
		V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	1	µA
I_{GSS}	gate leakage current	V_{DS} = 0 V; V_{GS} = 20 V; T_j = 25 °C	-	2	100	nA
		V_{DS} = 0 V; V_{GS} = -20 V; T_j = 25 °C	-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see Figure 11	-	-	8	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 11; see Figure 12	-	3.4	4	mΩ
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	I_D = 25 A; V_{DS} = 32 V; V_{GS} = 10 V; T_j = 25 °C; see Figure 13; see Figure 14	-	97	-	nC
Q_{GS}	gate-source charge		-	21	-	nC
Q_{GD}	gate-drain charge	I_D = 25 A; V_{DS} = 32 V; V_{GS} = 10 V; T_j = 25 °C; see Figure 14; see Figure 13	-	35	-	nC
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; T_j = 25 °C; see Figure 15	-	4391	5708	pF
C_{oss}	output capacitance		-	800	1040	pF
C_{rss}	reverse transfer capacitance		-	535	696	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 30 V; R_L = 1.2 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 10 Ω; T_j = 25 °C	-	40	-	ns
t_r	rise time		-	95	-	ns
$t_{d(off)}$	turn-off delay time		-	129	-	ns
t_f	fall time		-	92	-	ns
L_D	internal drain inductance	from drain lead 6 mm from package to centre of die ; T_j = 25 °C	-	4.5	-	nH
		from contact screw on mounting base to centre of die ; T_j = 25 °C	-	3.5	-	nH
L_S	internal source inductance	from source lead to source bond pad ; T_j = 25 °C	-	7.5	-	nH
Source-drain diode						
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; see Figure 16	-	0.83	1.2	V
t_{rr}	reverse recovery time	I_S = 20 A; dI_S/dt = -100 A/µs; V_{GS} = -10 V; V_{DS} = 30 V; T_j = 25 °C	-	44	-	ns
Q_r	recovered charge		-	57	-	nC

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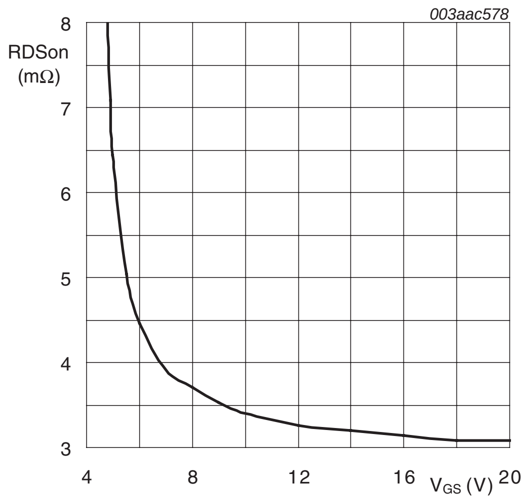
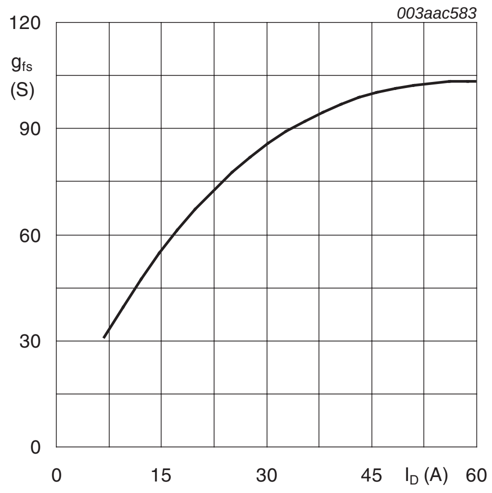


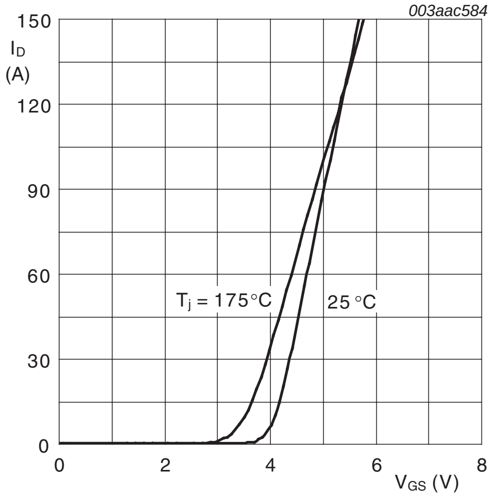
$T_j = 25\,°C; I_D = 25A$

Fig 5. Drain-source on-state resistance as a function of gate voltage; typical values



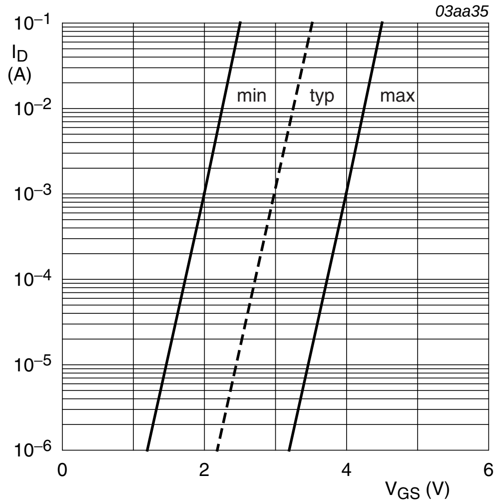
$T_j = 25\,°C; V_{DS} = 25V$

Fig 6. Forward transconductance as a function of drain current; typical values



$V_{DS} = 25V$

Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$T_j = 25\,°C; V_{DS} = 5V$

Fig 8. Sub-threshold drain current as a function of gate-source voltage

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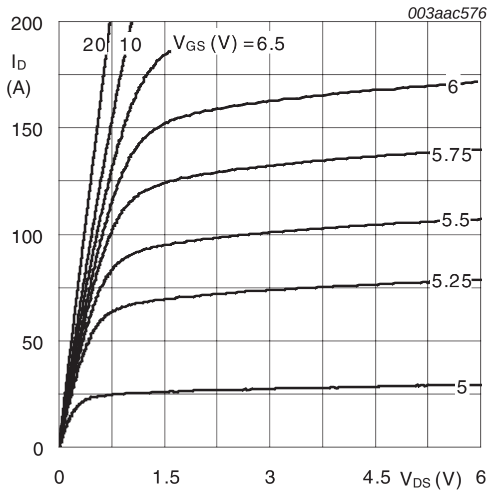
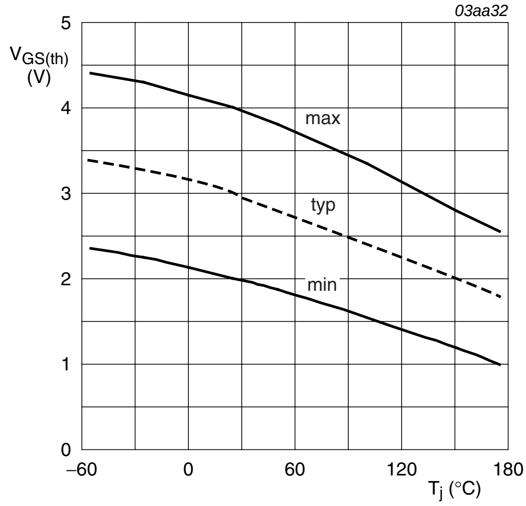


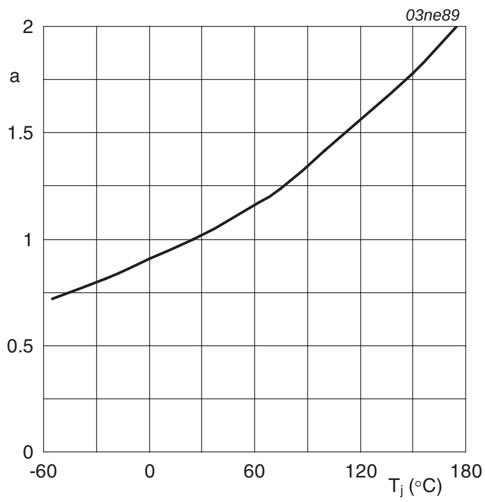
$T_j = 25°C$

Fig 9. Output characteristics: drain current as a function of drain-source voltage; typical values



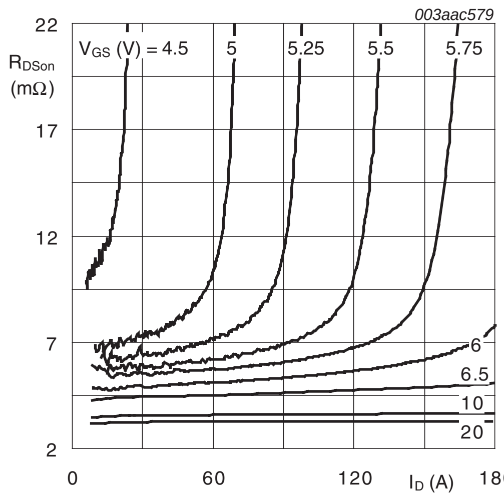
$I_D = 1mA; V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature



$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

Fig 11. Normalized drain-source on-state resistance factor as a function of junction temperature



$T_j = 25°C$

Fig 12. Drain-source on-state resistance as a function of drain current; typical values

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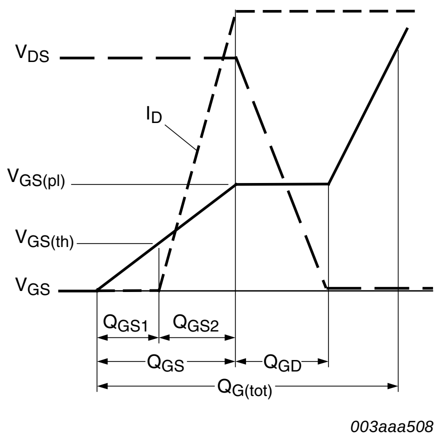
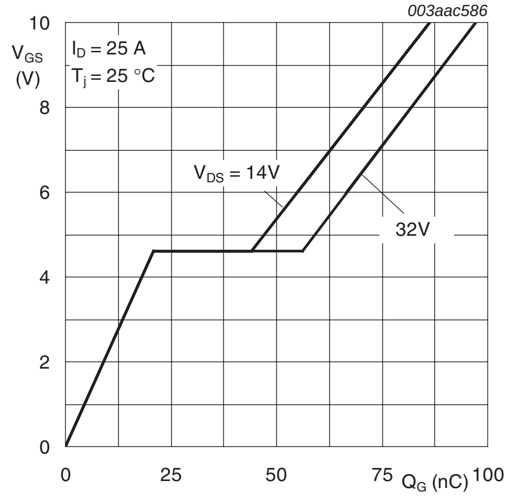
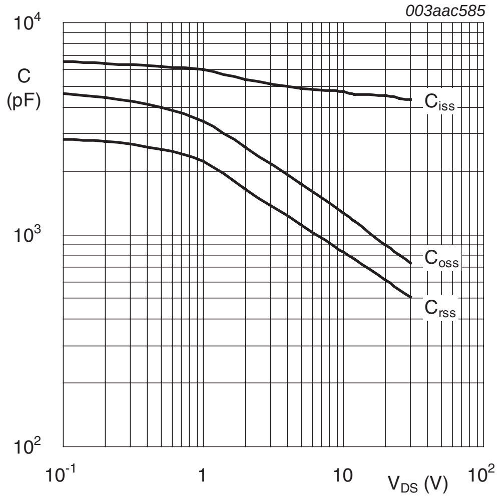


Fig 13. Gate charge waveform definitions



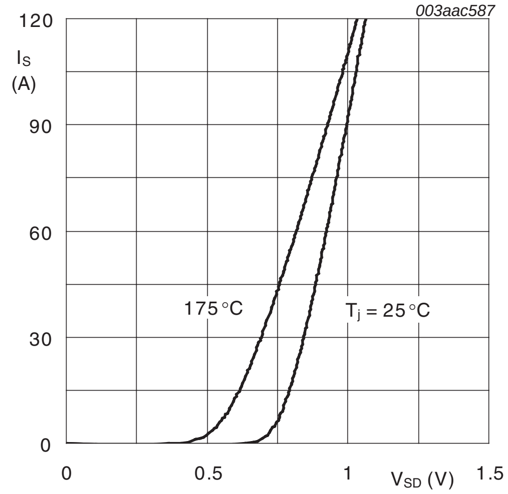
$T_j = 25\,°C$

Fig 14. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0V; f = 1MHz$

Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0V$

Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

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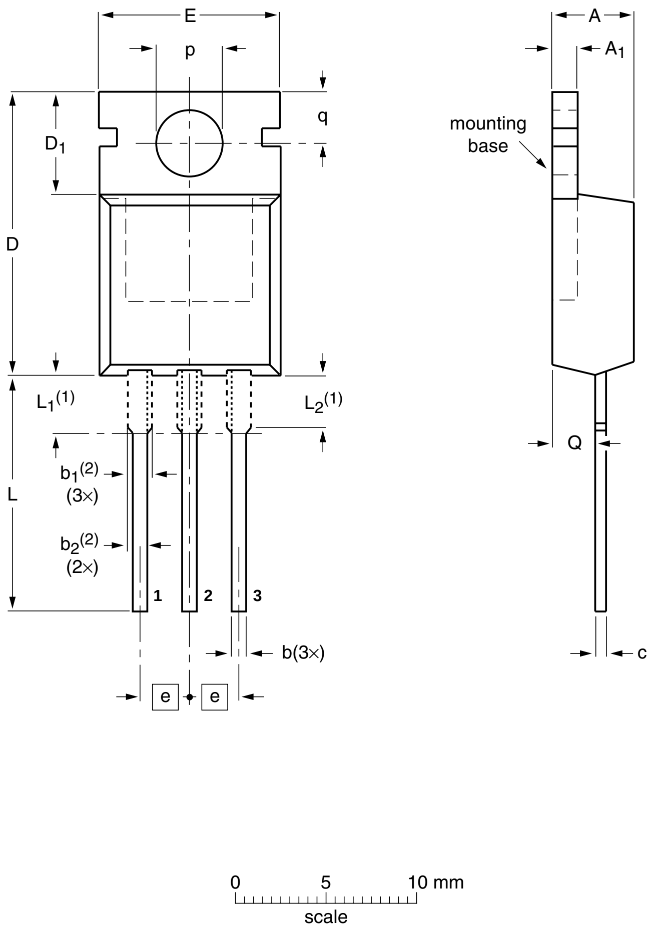
7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB **SOT78**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	$b_1^{(2)}$	$b_2^{(2)}$	c	D	D_1	E	e	L	$L_1^{(1)}$	$L_2^{(1)}$ max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

1. Lead shoulder designs may vary.
2. Dimension includes excess dambar.

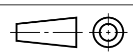
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			~~08-04-23~~ 08-06-13

Fig 17. Package outline SOT78 (TO-220AB)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK754R0-40C v.2	20100720	Product data sheet	-	BUK754R0-40C v.1
Modifications:	• Status changed from preliminary to product. • Various changes to content.			
BUK754R0-40C v.1	20090114	Preliminary data sheet	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Date of release: 20 July 2010

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